## NSN 5961-01-075-2169

Transistor - Page 1 of 1

No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-075-2169 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches Overall Diameter: 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 breakdown voltage, collector-to-base, emitter open and 250.0 breakdown voltage, collector-to-base, emitter open and 5.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** Between 4.00 amperes source cutoff current and 10.00 amperes source cutoff current **Power Rating Per Characteristic:** 125.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:**